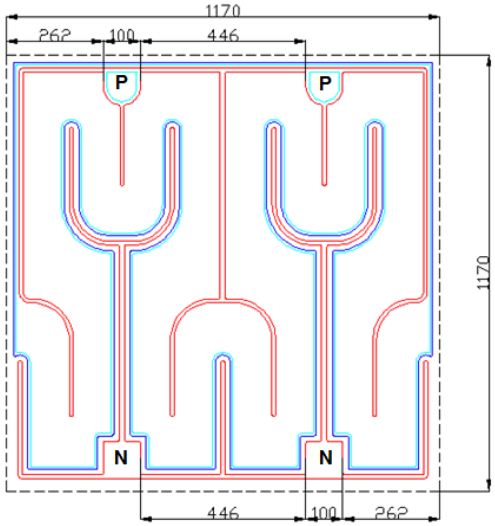
InGaN High Power Blue Chip
Model NO.: SIRIUS-45J



General Description:

(1) Chip Dimension

Chip Size= 45.0 mil x 45.0 mil (1170um x 1170um)

Chip Thickness= 150±10μm

P Bonding Pad= 100±10μm

N Bonding Pad= 100±10μm

(2) Electrode:

P (Anode) → Au

N (Cathode) → Au

(3) Structure:

Backside metal reflector

SiO_2 Passivated surface

Electro-optical Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Forward Voltage	V_F	-	3.4	4.0	V	I_F=350mA
Dominant Wavelength	λ_D	450	-	467.5	nm	I_F=350mA
Reverse Current	I_R	0	-	2	μA	V_R=-5V

Lunimous Intensity(I_V) mcd at I_F=350mA	Dominant Wavelength(nm)											
Range	445~447.5	447.5~450	450~452.5	452.5~455	455~457.5	457.5~460	460~462.5	462.5~465	465~467.5	467.5~470	470~472.5	472.5~475
2200-2400			*									
2400-2600			*	*								
2600-2800			*	*	*							
2800-3000				*	*	*						
3000-3300					*	*	*					
3300-3600						*	*	*				
3600-3900						*	*	*	*			
3900-4200							*	*	*			
4200-4500								*	*			

Features:

1. High Luminous Intensity
2. Long Operation Life
3. High Current; Pulse Operation
4. Indoor/Outdoor Applications

Notes:

1. Dominant wavelength includes an error of ± 1nm
2. Luminous intensity includes an error of ±10%
3. Luminous intensity is measured on bare chip
4. InGaN LED is sensitive to ESD

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